

SA data sheet SA-2800-10-x, λ = 2800 nm

Saturable absorber in transmission

Laser wavelength		λ = 2500 nm 3000 nm
Absorptance		A ₀ = 10 % @ 2.8 μm
Transmittance		T ₀ = 90 % @ 2.8 μm
Reflectance		R ₀ = 0 % @ 2.8 μm
Modulation depth		ΔT = 6 % @ 2.8 μm
Non-saturable loss		A _{ns} = 4 % @ 2.8 μm
Saturation fluence		Φ_{sat} = 300 µJ/cm ²
Damage threshold		$\Phi = 2 \text{ mJ/cm}^2$
Relaxation time constant		τ ~ 10 ps
Chip area		5 mm x 5 mm; other dimensions on request
Chip thickness		625 μm semi-insulating GaAs
Front side protection		AR coating for 2.8 µm
Back side coating		the SA back side is polished and antireflection coated for 2.8 μm
Mounting of SA	x = 0 x = 12.7 g x = 25.4 g	denotes the type of mounting as follows: unmounted glued on a Cu-cylinder with 12.7 mm \varnothing and 4 mm \varnothing center hole glued on a Cu-cylinder with 25.4 mm \varnothing and 4 mm \varnothing center hole

100 · reflectance, transmittance, absorptance [%] 90 80 reflectance 70 transmittance absorptance 60 50 40 · 30 20 10 0 **1**.... **1**. 0 wavelength [nm] Wafer 701-II

Spectral low intensity transmittance, reflectance and absorptance





